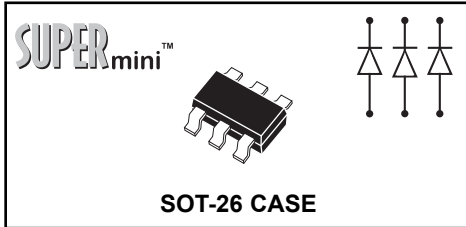


CMXD4448
SURFACE MOUNT
SUPERmini™
TRIPLE ISOLATED
HIGH SPEED
SILICON SWITCHING DIODES



Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD4448 type contains three (3) Isolated High Speed Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a super-mini surface mount package, designed for applications requiring high speed switching applications.

MARKING CODE: X48

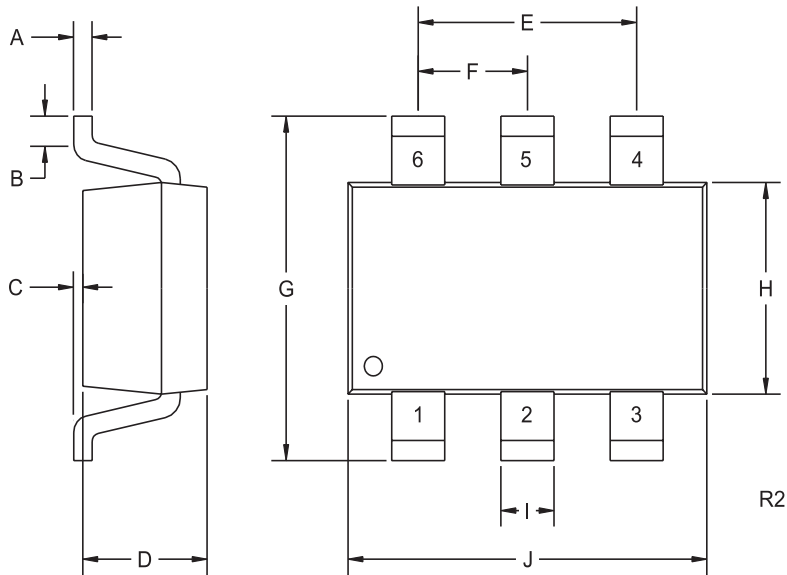
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, $t_p=1 \mu\text{sec.}$	I_{FSM}	4000	mA
Forward Surge Current, $t_p=1 \text{ sec.}$	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C/W}$

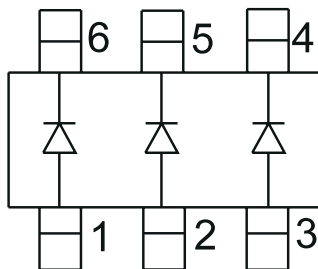
ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=20\text{V}$		25	nA
BV_R	$I_R=5.0\mu\text{A}$	75		V
BV_R	$I_R=100\mu\text{A}$	100		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1 \text{ MHz}$		4.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\Omega \text{ Rec. to } 1.0\text{mA}$		4.0	ns

SOT-26 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

LEAD CODE:

- 1) ANODE 1
- 2) ANODE 2
- 3) ANODE 3
- 4) CATHODE 3
- 5) CATHODE 2
- 6) CATHODE 1

MARKING CODE: X48

R2 (14-November 2002)